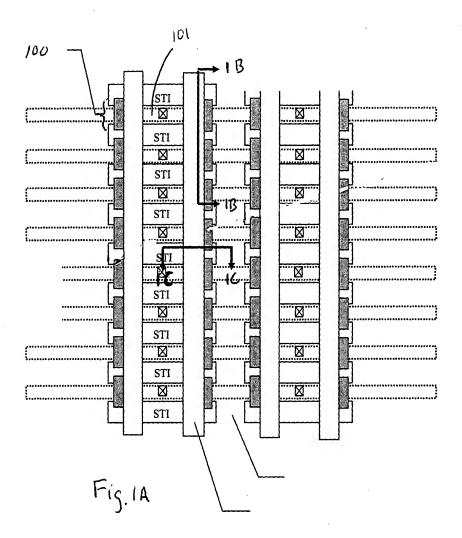
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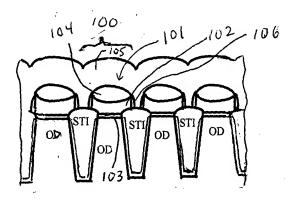


Fig. 1B

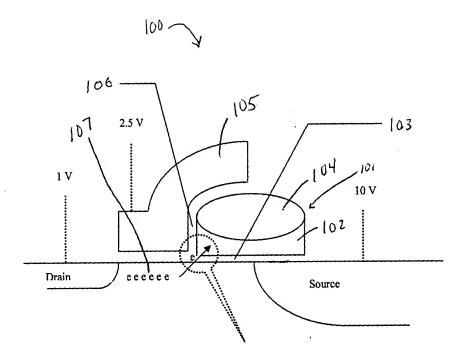
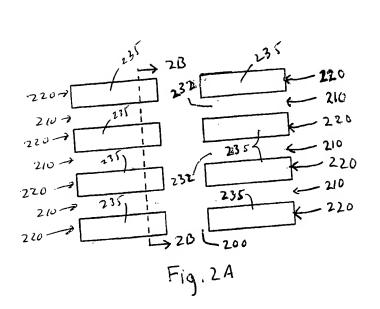


Fig.1C

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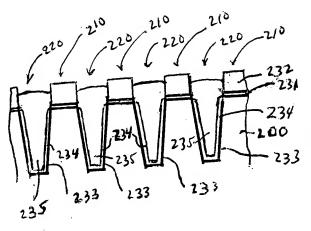


Fig. 2B

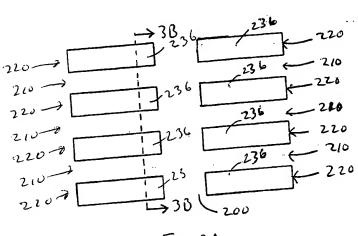


Fig. 3A

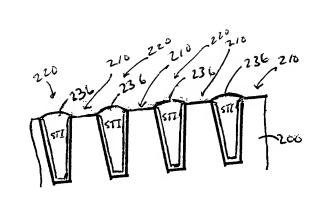
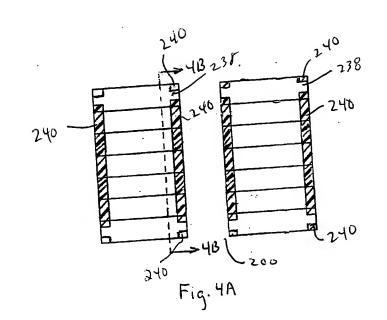


Fig. 3B



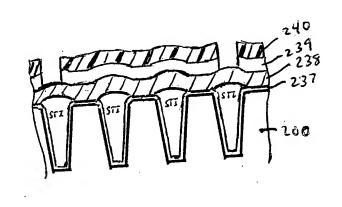
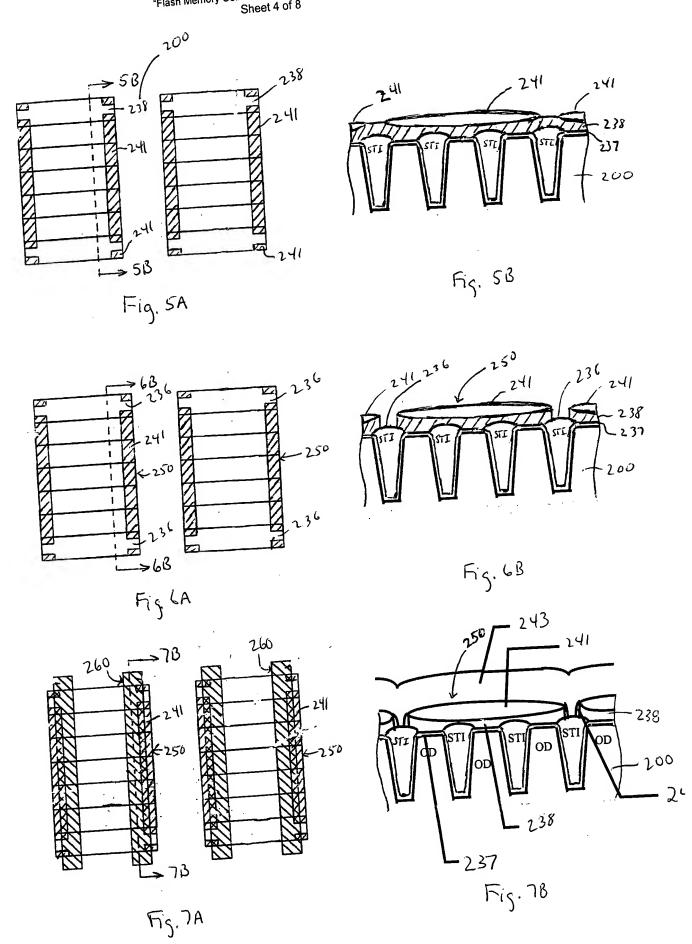
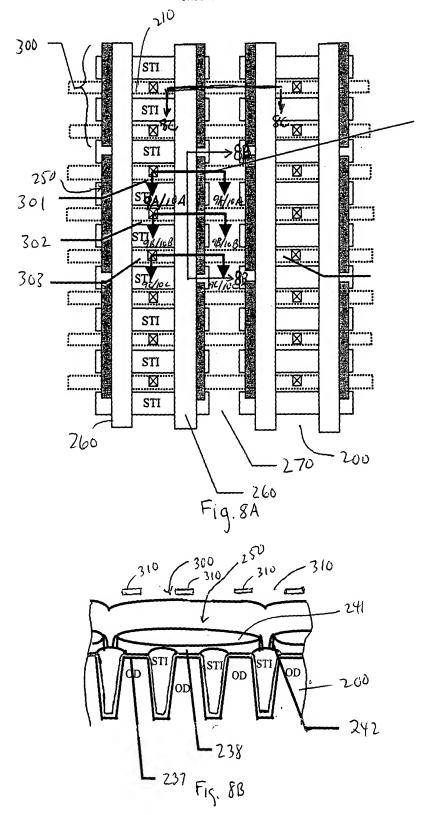


Fig. 43

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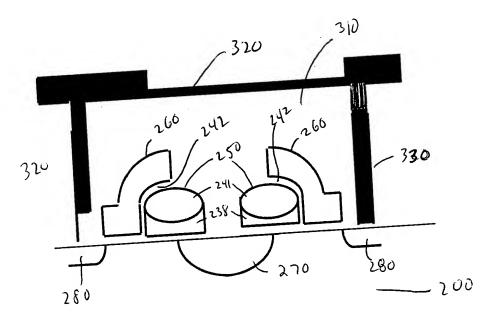
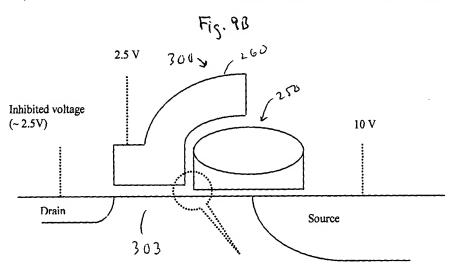


Fig. 8C

Docket No. N1085-00125 Inventors: Chia-Ta Hsieh et al. "Flash Memory Cell Having Multi-Program Channels" Sheet 7 of 8 300-2.5 V 1 V 10 V Drain Source 280 301 electron trapping 270 Fig. 9A 2.5 V 3002 Inhibited voltage (~2.5V) 10 V

Channel turn off, so there are not electron trapping

Source

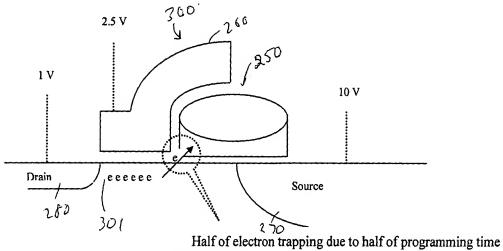


Drain

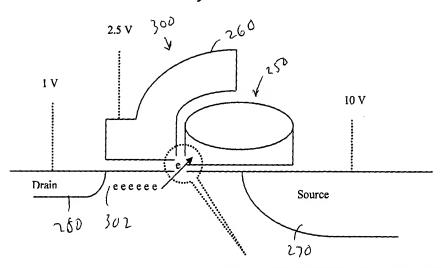
302

Channel turn off, so there are not electron trapping

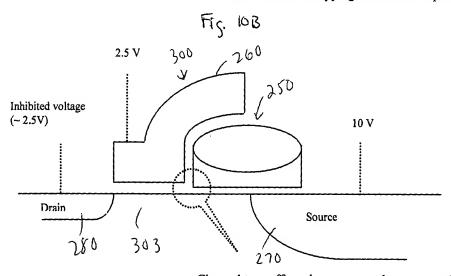
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Half of electron trapping due to half of programming time Fig. 10 A



Half of electron trapping due to half of programming time



Channel turn off, so there are not electron trapping $F_{i,j}$. 10 L